2SB0953 (2SB953), 2SB0953A (2SB953A)

Silicon PNP epitaxial planar type

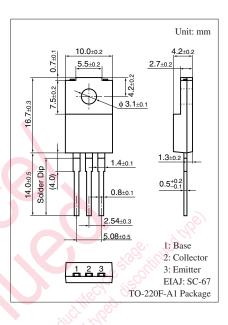
For low-voltage switching

Features

- \bullet Low collector-emitter saturation voltage $V_{\mbox{CE(sat)}}$
- High-speed switching
- Full-pack package which can be installed to the heat sink with one screw

Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage	2SB0953	V _{CBO}	-40	V
(Emitter open)	2SB0953A		-50	
Collector-emitter voltage	2SB0953	V _{CEO}	-20	V
(Base open)	2SB0953A		-40	
Emitter-base voltage (Collector open)		V _{EBO}	-5	V
Collector current	I _C	-7	А	
Peak collector current	I _{CP}	-12	A	
Collector power		P _C	30	W
dissipation	$T_a = 25^{\circ}C$		2	
Junction temperature		Tj	150	°C
Storage temperature		T _{stg}	-55 to +150	°C



Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

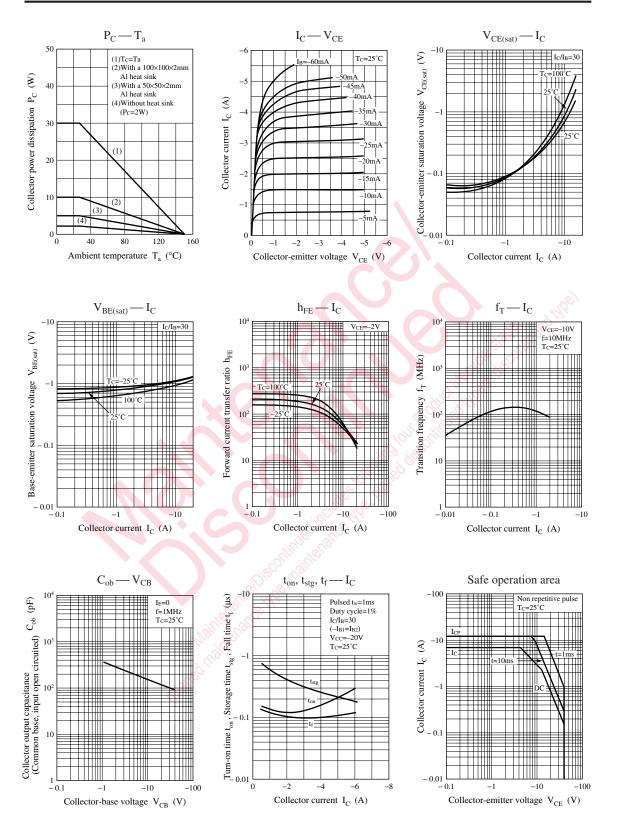
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SB0953	V _{CEO}	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = 0$	-20			V
(Base open)	2SB0953A		Sinc. State	-40			
Collector-base cutoff	2SB0953	I _{CBO}	$V_{CB} = -40 \text{ V}, I_E = 0$			-50	μΑ
current (Emitter open)	2SB0953A		$V_{CB} = -50 \text{ V}, I_E = 0$			-50	
Emitter-base cutoff current (Col	lector open)	I _{EBO}	$V_{EB} = -5 V, I_C = 0$			-50	μΑ
Forward current transfer rat	io	h _{FE1}	$V_{CE} = -2 V, I_C = -0.1 A$	45			
		h _{FE2} *	$V_{CE} = -2 V, I_C = -2 A$	60		260	
Collector-emitter saturation	voltage 🚿	V _{CE(sat)}	$I_C = -5 A, I_B = -0.16 A$			- 0.6	V
Base-emitter saturation volt	age	V _{BE(sat)}	$I_{C} = -5 A, I_{B} = -0.16 A$			-1.5	V
Transition frequency	don a	f _T	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 10 \text{ MHz}$		150		MHz
Collector output capacitance		C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		140		pF
(Common base, input open	circuited)						
Turn-on time		t _{on}	$I_{C} = -2 A$, $I_{B1} = -66 mA$, $I_{B2} = 66 mA$		0.1		μs
Storage time		t _{stg}	$V_{CC} = -20 V$		0.5		μs
Fall time		t _f			0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

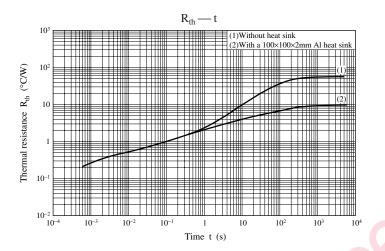
Rank	R	Q	Р	
h _{FE2}	60 to 120	90 to 180	130 to 260	

Note) The part numbers in the parenthesis show conventional part number.

Panasonic



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